

Listing of Claims and Amendments thereto:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of packaging electronic devices that operate based on acoustic waves, comprising the steps of:

providing a cap wafer having a surface;

lithographically forming raised ridges on the cap wafer surface at areas near a perimeter of a desired cavity region so that the raised ridges are a contiguous part of said cap wafer~~forming raised ridges on the cap wafer~~ surface;

printing a glass frit material on the raised ridges; and

bonding, via said glass frit material at each raised ridge, ~~said the~~ cap wafer surface to a substrate surface containing electronic devices,

each raised ridge using surface tension to hold the glass frit to a higher and thinner frit line width dimension, and to prevent lateral flow of the glass frit, than if the frit were deposited directly on a flat cap wafer surface without lithographically formed raised ridges.

2. (Cancel)

3. (Cancel)

4. (Cancel)

5. (Original) The method of claim 4, wherein a linewidth of the frit is less than 125 μm .

6. (Cancel)

7. (Currently Amended) The method of claim 1, wherein bonding areas when the raised ridges are bonded form a continuous perimeter around the device, so that a hermetic seal is formed.

8. (Currently Amended) A method of packaging electronic devices operating based on acoustic waves, comprising the steps of:

providing a cap wafer having a surface;

~~The method of claim 1, said step of forming further including the steps of:~~

trenching recesses into ~~said the~~ cap wafer surface at areas near the perimeter of a desired cavity region;

printing material into ~~said the~~ recesses and planarizing it such that each filled recess is flush with the cap wafer surface; and

etching away the cap wafer surface, except for the areas of the original recesses, so that the material forms the raised ridges that are bonded to the substrate surface.

9. (Currently Amended) The method of claim 8, wherein each raised ridge is formed slightly inboard from the perimeter of a desired cavity region, each raised ridge composed of a glass frit material for bonding ~~said the~~ cap wafer to ~~said the~~ substrate.

10. (Original) The method of claim 9, wherein a linewidth of the frit is less than 125 μm .

11. (Currently Amended) The method of claim 8, wherein, after ~~said the~~ recesses are formed and the recesses are filled, ~~said the~~ raised ridges are fabricated to any desired height, width and location on said cap wafer surface by etching the surrounding cap wafer surface surrounding each filled recess.

12. (Original) The method of claim 8 wherein the ridges form a continuous perimeter around a cavity region such that a hermetic seal is made when the cap wafer is bonded to a wafer of an electronic device.